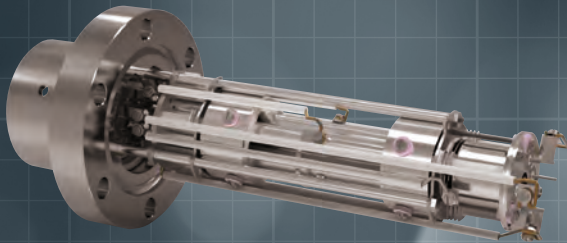


EQP

Analysis of the reaction kinetics of plasma assisted ALD processes

ALD

ATOMIC LAYER DEPOSITION – VACUUM PROCESSING OF THIN FILMS



HMT

Residual gas analysis at high pressure



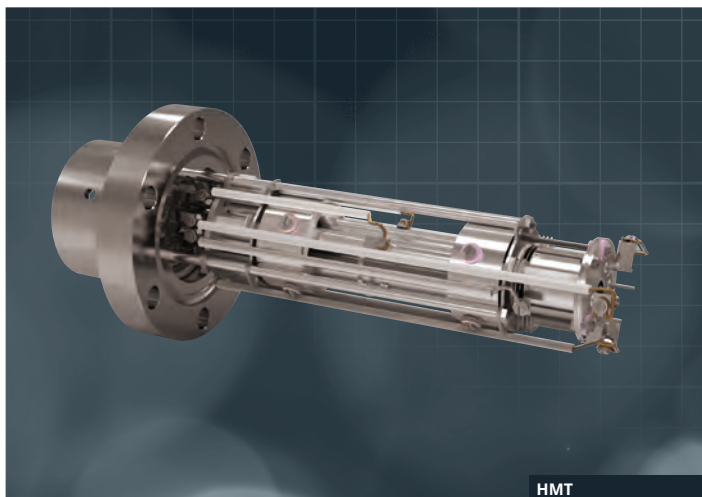
HPR-30^{ALD}

Vacuum process gas analysis
– wide sampling pressure range

AutoSIMS

ALD film
analytics





HMT

Residual gas analysis at high pressure

- ▶ HMT mode for high pressure operation to 5×10^{-3} mbar
- ▶ RGA mode for high sensitivity operation to 10^{-13} mbar
- ▶ 100 amu mass range
- ▶ Stability better than +/- 1% over 24 hours
- ▶ Fast access mixed mode scanning
- ▶ Real-time background subtraction



EQP

Analysis of the reaction kinetics of plasma assisted ALD processes

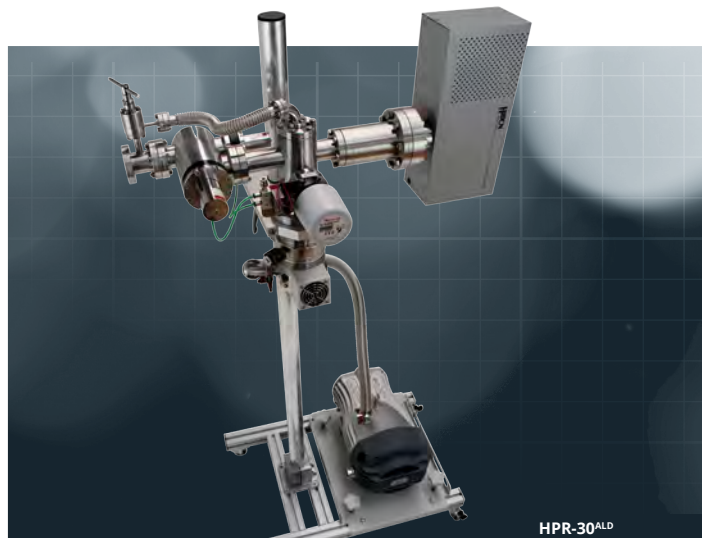
- ▶ +ve and -ve ion analysis
- ▶ Mass resolved ion energy analysis
- ▶ Neutrals and neutral radical analysis
- ▶ Energy resolved mass analysis
- ▶ Mass range options to 1000 amu
- ▶ Energy range options to 1000 eV



AutoSIMS

ALD film analytics

- ▶ Composition, contamination, diffusion and interface analysis
- ▶ Nanometre depth resolution
- ▶ Tool for research and production
- ▶ TPD – Tool for temperature programmed desorption



HPR-30^{ALD}

Vacuum process gas analysis – wide sampling pressure range

- ▶ Pump-down Profiles
- ▶ Vacuum Diagnostics
- ▶ Real-time Precursor Analysis
- ▶ Residuals
- ▶ Backfill
- ▶ Bakeout Endpoint Confirmation
- ▶ Leak Checking